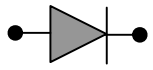
Capsule Type Rectifier Diode SHXXC1130



Symbol	Characteristics	Conditions	T_J(^{0}C)	Value	Unit
BLOCKING PARAMETERS					
V_{RRM}	Repetitive peak reverse voltage		160	200-1800	V
I_{RRM}	Repetitive peak reverse current	V = V_{RRM}	160	30	mA
CONDUCTING PARAMETERS					
$I_{F(AV)}$	Average on-state current	180 sine, 50H$_Z$, T_C = 65^{0}C		1130	A
I_{RMS}	RMS on-state current			1775	A
I_{FSM}	Non repetitive peak surge on-state current	Sine wave, 10mS without reverse voltage	160	11000	A
I^2t	Permissible surge energy			605	kA^{2}S
V_{FM}	Peak on-state voltage drop	On-state current = 3000A	160	1.83	V
V_0	Typical forward conduction Threshold voltage		160	0.78	V
r_0	Typical forward slope resistance		160	0.35	mΩ
THERMAL & MECHANICAL PARAMETERS					
$R_{TH\ (J-C)}$	Thermal impedance, 180^0 conduction, Sine	Junction to case		0.045	^{0}C/W
$R_{TH\ (C-HK)}$	Thermal impedance	Case to heatsink		0.015	^{0}C/W
T_J	Maximum Permissible junction temperature			160	^{0}C
T_{STG}	Storage temperature range			-40 – 160	^{0}C
F	Mounting Torque			6.5	KN
W	Weight			90	gms

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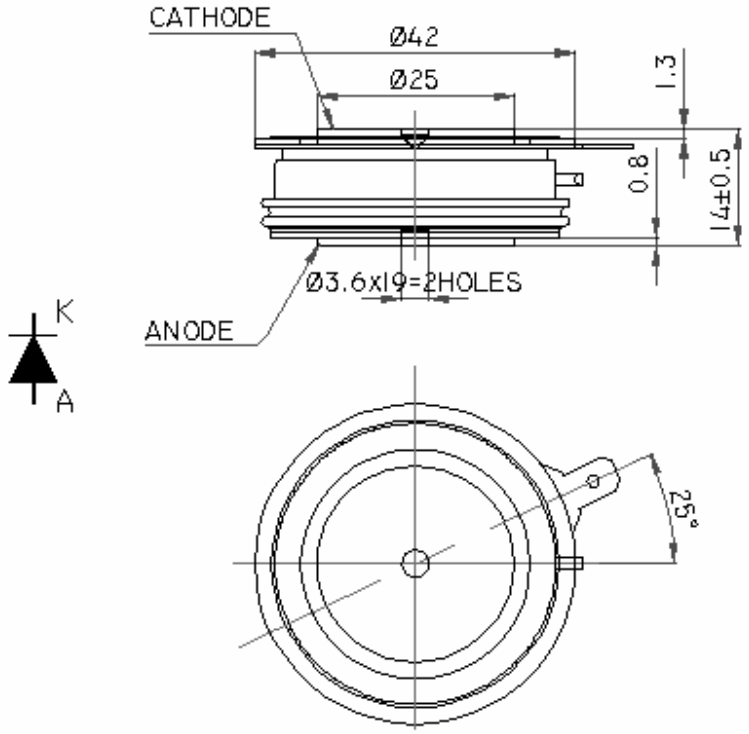
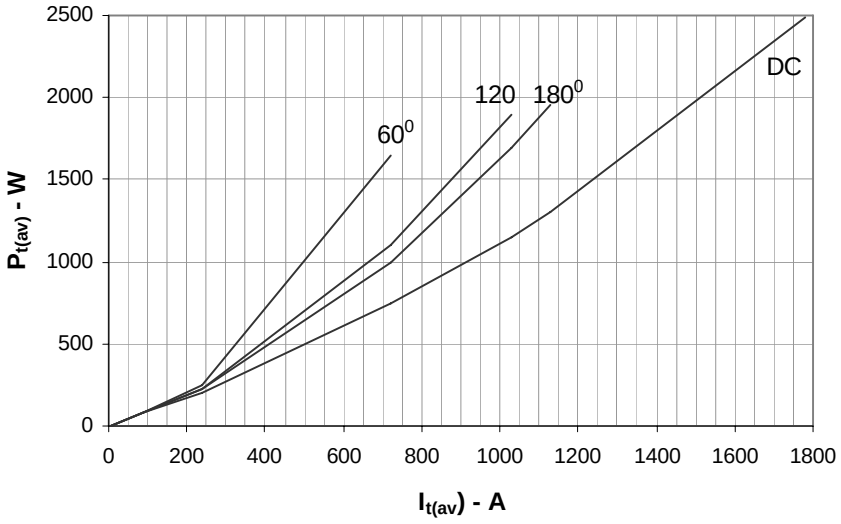


All dimensions in mm

On State Power Loss



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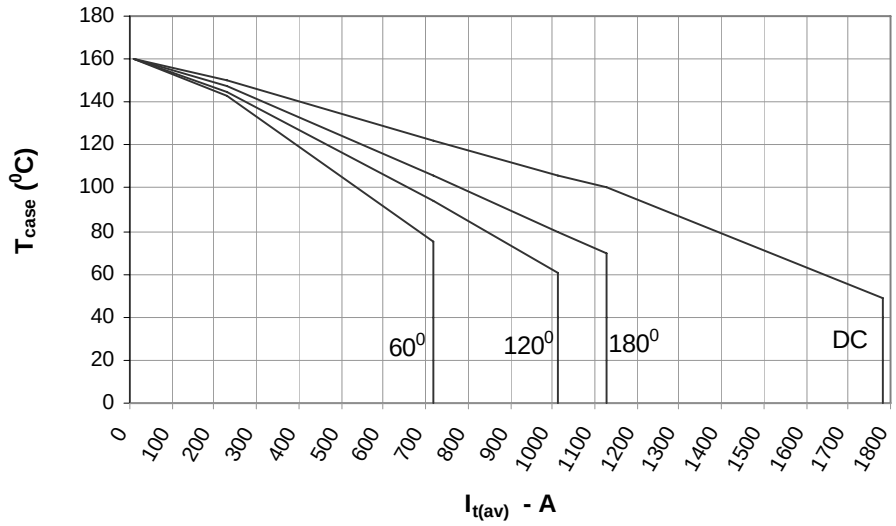
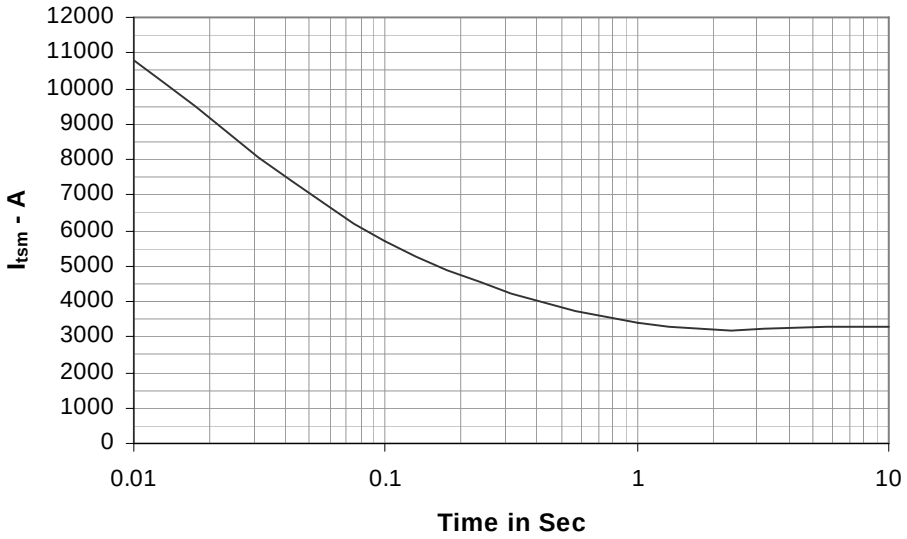
Maximum Permissible Case Temp



Max non repetitive Surge Current



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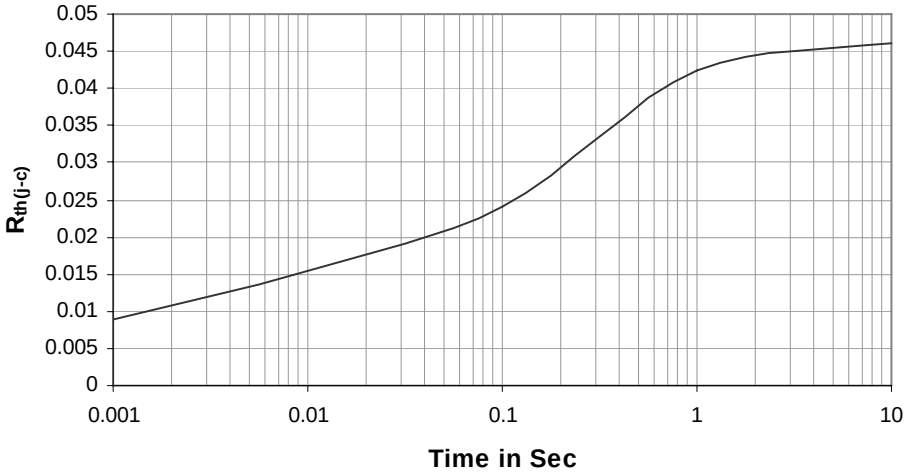
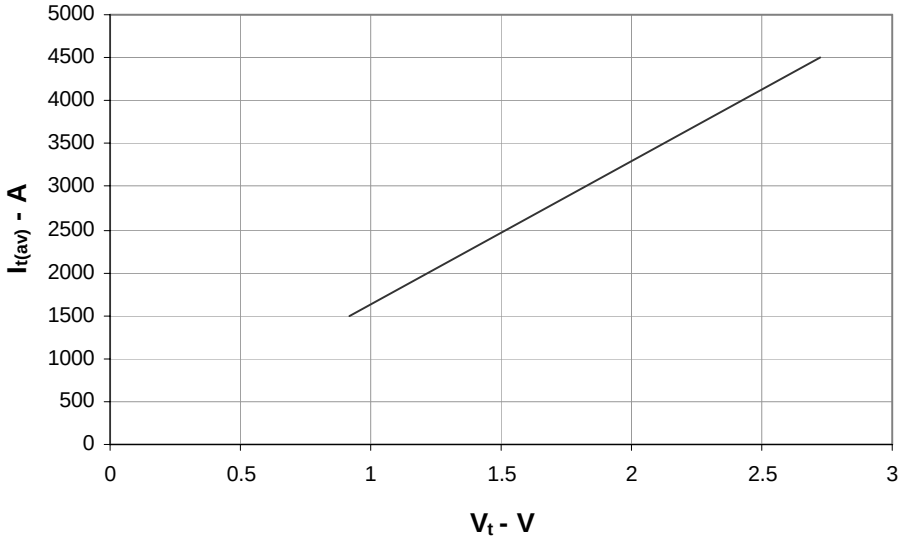
Transient Thermal Impedance Junction to Case



On State Characteristics



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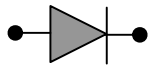

Ordering Information: -

SH	XX	C	1130
Hirect make Capsule Diode	V_{RRM} = XX * 100 e.g.12 * 100 =1200V	Capsule Diode	$I_{F(AV)}$ = 1130A

Hind Rectifiers Ltd reserves the right to change the specifications without notice.

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